

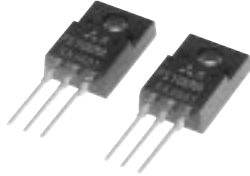
**PRELIMINARY**  
 Notice: This is not a final specification.  
 Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

# FS16KMA-5A

HIGH-SPEED SWITCHING USE

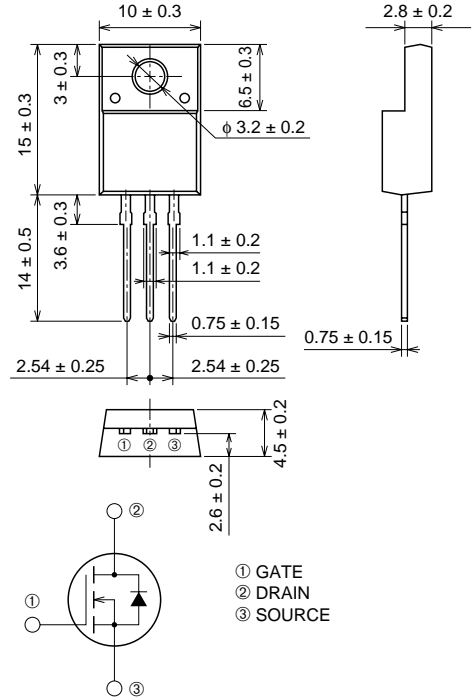
## FS16KMA-5A



- 10V DRIVE
- V<sub>DSS</sub> ..... 250V
- r<sub>DS (ON)</sub> (MAX) ..... 0.25Ω
- I<sub>D</sub> ..... 16A

## OUTLINE DRAWING

Dimensions in mm



TO-220FN

## APPLICATION

Cs Switch for CRT Display monitor

## MAXIMUM RATINGS (T<sub>c</sub> = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>DSS</sub>	Drain-source voltage	V <sub>GS</sub> = 0V	250	V
V <sub>GSS</sub>	Gate-source voltage	V <sub>DS</sub> = 0V	±20	V
I <sub>D</sub>	Drain current		16	A
I <sub>DM</sub>	Drain current (Pulsed)		48	A
I <sub>DA</sub>	Avalanche drain current (Pulsed)	L = 200μH	16	A
P <sub>D</sub>	Maximum power dissipation		35	W
T <sub>ch</sub>	Channel temperature		-55 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-55 ~ +150	°C
V <sub>iso</sub>	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

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**ELECTRICAL CHARACTERISTICS** (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	250	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±10	μA
IDSS	Drain-source leakage current	VDS = 250V, VGS = 0V	—	—	1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	2.0	3.0	4.0	V
rDS (ON)	Drain-source on-state resistance	Id = 8A, VGS = 10V	—	0.19	0.25	Ω
VDS (ON)	Drain-source on-state voltage	Id = 8A, VGS = 10V	—	1.52	2.00	V
yfs	Forward transfer admittance	Id = 8A, VDS = 10V	—	16.0	—	S
Ciss	Input capacitance	VDS = 25V, VGS = 0V, f = 1MHz	—	1850	—	pF
Coss	Output capacitance		—	180	—	pF
Crss	Reverse transfer capacitance		—	50	—	pF
td (on)	Turn-on delay time		—	30	—	ns
tr	Rise time	VDD = 150V, Id = 8A, VGS = 10V, RGEN = RGS = 50Ω	—	50	—	ns
td (off)	Turn-off delay time		—	320	—	ns
tf	Fall time		—	70	—	ns
VSD	Source-drain voltage	IS = 8A, VGS = 0V	—	0.95	—	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	3.57	°C/W